

CaB₆: a new semiconducting material for spin electronics.

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Ferromagnetism was recently observed at unexpectedly high temperatures in La-doped CaB₆. The starting point of all theoretical proposals to explain this observation is a semimetallic electronic structure calculated for CaB₆ within the local density approximation. Here we report the results of parameter-free quasiparticle calculations of the single-particle excitation spectrum which show that CaB₆ is not a semimetal but a semiconductor with a band gap of 0.8 eV. Magnetism in La_xCa_{1-x}B₆ occurs just on the metallic side of a Mott transition in the La-induced impurity band.

The recent observation of ferromagnetism in La doped alkaline-earth hexaboride compounds at high temperatures [1] presents three puzzles. Firstly, ferromagnetism is usually associated with elements with a partly filled 3d, 4f or 5f shell. Secondly, ferromagnetic ordering is only observed for a narrow dopant concentration range and for a surprisingly low dopant concentration. The maximum observed moment in Ca_{1-x}La_xB₆ is 0.07 Bohr magnetons per La atom for $x = 0.005$. Thirdly, and most surprising of all is the observation of very large Curie temperatures; for La_{0.01}Ca_{0.99}B₆ a value close to 900 K has recently been reported [2]. Such a large value virtually excludes the possibility of the observed magnetism being related to magnetic impurities.

In an initial comment on the experimental observations, Ceperley suggested [3] that it might be an example of the long-predicted but never observed ferromagnetic phase of a dilute electron gas; improved calculations increase the estimated density at which this might occur [4]. An alternative explanation proposed by Zhitomirsky was that the ferromagnetic hexaborides might be doped excitonic insulators [5]. This explanation requires that the exciton binding energy should be comparable in size to the single-particle band gap. Jarlborg suggested [6] that the magnetism may be conventional itinerant magnetism. Although magnetism in materials which do not have partly filled d or f shells is rare, it is not unprecedented. A handful of materials does exist, of which ZrZn₂ is the best known example, in which the Fermi energy falls at or close to an exceptionally narrow peak in the electronic density of states so that the Stoner criterion for the occurrence of itinerant magnetism is fulfilled. The problem posed by the hexaborides is not so much the occurrence of magnetic ordering but rather the strength of the magnetic coupling as reflected by the very high Curie temperature, and this was not estimated.

All three suggestions are based on electronic structure calculations which indicate that stoichiometric CaB₆ is

a semimetal with a very small overlap between the conduction and valence bands [7–9] or might have a very small gap [7]. Since the theoretical predictions rely on details of this electronic structure, it is important to examine their validity. Massidda's and Rodriguez' studies of the electronic structure were based on the FLAPW calculation method which is probably the most accurate available. These calculations were carried out within the framework of density functional theory (DFT) using the local density approximation (LDA). Such calculations are known to be capable of yielding total energies with a very useful accuracy. However, it is also well known that the eigenvalue spectrum which results from solving the Kohn-Sham equations of DFT cannot be interpreted unreservedly as an excitation spectrum [13,14] and sometimes the results are spectacularly wrong. In particular, the band gaps of semiconductors are typically underestimated by 50% and in extreme cases such as Ge the conduction and valence bands are found to overlap resulting in metallic or semimetal character.

In order to study single-particle excitations, one should solve Dyson's equation for the single-particle Green's function expressed in terms of the self-energy operator Σ . Σ can be expanded as a perturbation series in the Green's function G and the dynamically screened Coulomb interaction W . The so-called *GW* approximation introduced by Hedin [15] includes only the first term in this series. In addition, one usually assumes a quasi-particle (QP) expression for the Green's function G . For a large number of semiconductors and insulators such calculations produce band gaps which are in very close quantitative agreement with experimental single-particle band gaps [16]. The main purpose of the present paper is to apply these parameter-free calculations with their proven predictive capability to CaB₆. From our results we shall conclude that, contrary to what is currently being assumed, the parent material is actually a semiconductor with quite a large band gap. This finding has far-

reaching consequences for understanding the basic properties of the doped, ferromagnetic phase and opens up the prospect of a range of novel applications.

The starting point for our *GW* study is an LDA calculation for CaB_6 performed with a plane-wave basis and using norm-conserving pseudopotentials to describe the interaction between the valence electrons and the ionic cores [17]. Using the experimentally determined structure, we reproduce essentially perfectly the energy bands calculated by Massidda [8] using an all-electron method. The results are shown in Fig. 1(a). There are ten valence bands (bonding orbitals derived from the boron 2s and 2p levels) well-separated from the conduction bands (antibonding states) with the exception of an overlap of about 0.3 eV in a small region around the X point of the highest occupied and lowest unoccupied bands. The occurrence of such small band overlap (or the presence of a comparably small band gap) is an important criterion for the stability of an excitonic insulator phase [5]. The effective masses in units of the free electron mass for the bands near X, $m_e^\perp = 0.22$ and $m_e^\parallel = 0.50$ for the electrons and $m_h^\perp = 0.20$ and $m_h^\parallel = 1.8$ for the holes, are close to values reported earlier [7,5]. We use the LDA electronic wave functions and eigenvalues as input for the *GW* calculations for which we adopt the space-time approach suggested by Rojas [18] in which all operators are represented on grids in real and reciprocal space, in the time and energy domains; details of our implementation have been given by van der Horst [19]. By varying the size of these grids we estimate that the calculated QP energies are converged within 0.1 eV. The densest grids we used were a $(12 \times 12 \times 12)$ real-space grid and a $(6 \times 6 \times 6)$ $\mathbf{k}$ -grid. The Green's function is constructed including the LDA wave functions and energies of the lowest 300 bands.

The results of the *GW* calculations are plotted in Fig. 1(b). Throughout the Brillouin zone, the QP corrections to particular LDA bands are rather uniform so that the dispersion of the *GW* bands is very similar to the LDA band dispersion and the effective masses differ only slightly from the values obtained from the LDA calculation. They are reduced on average by less than 10%, to $m_e^\perp = 0.20$ and $m_e^\parallel = 0.48$ for the electrons and $m_h^\perp = 0.17$ and $m_h^\parallel = 1.7$ for the holes. The sign and size of the corrections to the energy bands depend on their energy and their wavefunction character and vary considerably from band to band. Of particular importance are the relative shifts of the bands at X near the Fermi level. The hole band and electron bands are moved, respectively, downwards and upwards in energy resulting in the opening of a sizeable band gap of about 0.8 eV. The relative shifts can be understood from the bonding and antibonding character of the wave functions in the valence and conduction bands, respectively. This is quite analogous to the situation in silicon [20]. The largest

shift in the occupied bands is calculated for the lowest valence band which is lowered in energy by about 1.9 eV.

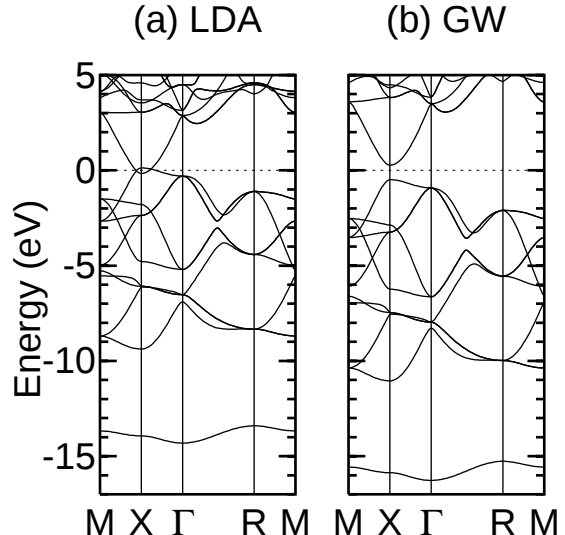


FIG. 1. Energy bands for CaB_6 in (a) the LDA approximation, (b) the *GW* approximation. The Fermi energy is indicated by the dotted line at 0 eV.

Our finding that bulk CaB_6 is a semiconductor is consistent with the large value of the low-temperature resistivity and with its increase with decreasing temperature recently reported by Ott [2] and by Vonlanthen [21] and also with recent results of angle-resolved photoemission experiments [22] in which a gap of a size similar to what we calculate was found. Because of the sensitivity of photoemission experiments to surface electronic structure, the authors interpreted their results exclusively in terms of the surface electronic structure. Our result indicates that there might indeed be a slight increase in the value of the band gap at the surface, something which is known to happen in heteropolar semiconductors.

The result for the stoichiometric phase has important implications for the models proposed to explain the ferromagnetism observed in the doped phase. Using our calculated values for the effective masses and static dielectric constant of 5, we obtain a scaled density parameter r_s of 1.5, and an exciton binding energy of about 0.07 eV. The scaled density parameter is still much lower than the values of 80 and 20 reported respectively, by Ceperley [3] and Ortiz [4], for which a ferromagnetic phase of the low density electron gas might be expected. The estimated excitonic binding energy is much smaller than the calculated QP band gap whereas the excitonic insulator models require them to be comparable in size [5]. Instead we note that the ferromagnetism occurs for an impurity concentration which is just on the metallic side of a Mott transition in the impurity band: $n^{1/3}a_H = 0.4$, where n is the dopant concentration 7×10^{19} electrons cm^{-3} and

$a_H = 10 \text{ \AA}$ is the Bohr radius of an isolated effective mass impurity.

Support for this possibility can be found in the very recent experimental studies on doped hexaborides reported by Terashima [23]. He found that some of his La-doped samples were paramagnetic, exhibiting the Curie-Weiss behaviour which is to be expected if the dopant concentration were below Mott's critical value. In other samples he found no indication of saturation of the magnetic moment even in the highest magnetic field reported (10 kOe). This behaviour might be expected for partly filled narrow bands. In addition Terashima found much larger values of the magnetic moment per dopant atom than reported by Young and Ott [1,2]. He also attributed a number of reported de Haas-van Alphen oscillation frequencies to Al inclusions. We note that it is extremely important to know where the La goes and if all of it actually occupies Ca sites as usually assumed since the effective valence of an impurity atom in a semiconductor is very sensitive to the local environment. Assuming that the magnetism occurs mainly in the impurity band, we are currently attempting to estimate the Curie temperature from total energy calculations and to determine the parameters which govern the physical behaviour of the doped system such as the hopping matrix elements, the charge and spin fluctuation parameters (Hubbard U and Stoner I, respectively) and the binding energy of the impurity state. The last quantity, the position of the impurity state with respect to the bottom of the conduction band, is particularly difficult to estimate reliably. It requires knowing the central cell potential which is known to make a substantial correction to the binding energy of the lowest effective mass states.

Irrespective of the origin of the high Curie temperature in the doped material, the existence of a large gap for the undoped material means a new class of magnetic semiconductors [10] is available with the unique characteristic of having a Curie temperature sufficiently high to allow room-temperature operation of semiconducting spin devices, something which has only very recently been achieved at low temperatures [11,12]. With the hexaborides it should be possible to inject a spin-polarized current from the doped into the undoped material in the ballistic regime and study the spin dynamics as a function of temperature, and of current density without the complication of having to apply an external magnetic field [11,12] or without the problems encountered when attempting to inject spins from a ferromagnetic metal into a conventional semiconductor in the diffusive regime [24]. It should also be possible to make a field-effect device to modulate a spin-polarized current in the doped hexaboride material and achieve gain. If a *p*-type hexaboride with some of the Ca replaced by a monovalent ion were also found to be ferromagnetic, it should even be possible to make the spin-analogues of bipolar devices.

Both Ca and B are light elements so that the spin-orbit

coupling is small. Since the lowest conduction band and highest valence band are both singly degenerate, the intrinsic spin-flip scattering should be weak with spin-flip scattering lengths comparable to what has recently been observed in carbon nanotubes [25]. Because of the small size of the spin-orbit coupling, because the magnetic moment is so tiny, and because the hexaborides are cubic, the material should be magnetically extremely soft with a very small intrinsic magnetocrystalline anisotropy. This could be important for sensor applications.

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